of EEE201

CMOS Digital Integrated Circuits

Department of Electrical & Electronic Engineering Xi'an Jiaotong-Liverpool University (XJTLU)

Monday, 9th December 2024

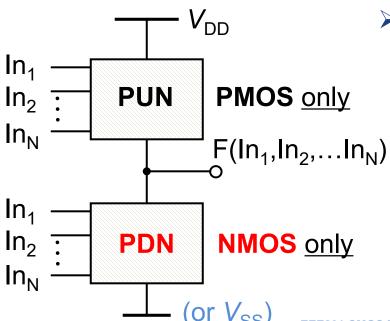
- ☐ Ratioed Logic
 - pull-up network replaced by a load
 - pseudo-NMOS
- ☐ Dynamic Logic & Domino Logic
 - precharge & evaluation phases



Combinational Logic Circuits

(pull-up & pull-down networks)

- □ In CMOS technology, a **combinational logic circuit** consists of basically a **pull-up network** (**PUN**) and a **pull-down network** (**PDN**).
 - The PUN consists of only PMOS transistors while PDN only NMOS transistors.

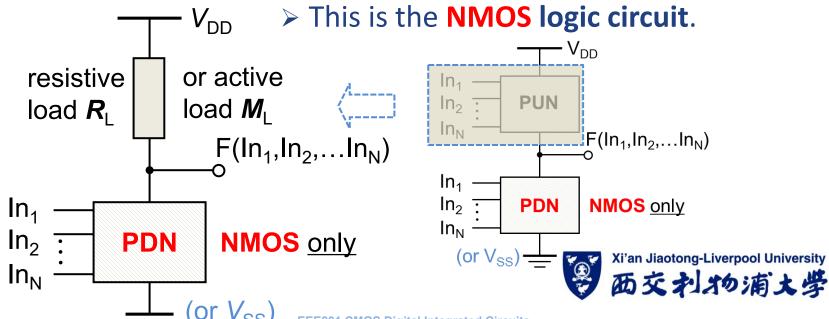


➤ In the <u>steady</u> state, either the PUN provides a low-resistance path to connect the output (F) to V_{DD} or the PDN make a low-resistance connection between the output and ground (or V_{SS}), hence *pulling up* or *down* the output voltage.

NMOS Combinational Logic Circuits

(pull-up network replaced with a load device)

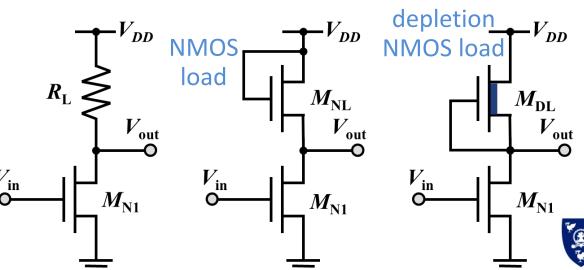
■ Before CMOS technology became mature, only one type of MOS transistors was available for implementation of digital integrated circuits. The pull-down network (PDN) consists of only NMOS transistors but the PUN is replaced by either a resistive load or an NMOS transistor as an active load.



NMOS Combinational Logic Circuits

(pull-down network fights with load device)

- □ In the NMOS logic circuits, when the pull-down network turns on, it "fights" with the resistive or active load to pull down the output voltage.
 - The **equivalent** load resistance should be high enough so that the NMOS pull-down network can pull down the output to an acceptably low logic "0" voltage V_{OI} .



➤ This can be understood with the VTC of the simple NMOS inverter.

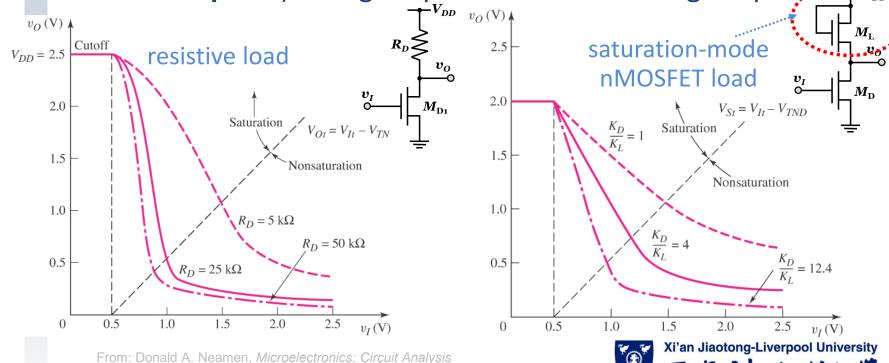


VTC of NMOS Inverters

& Design, 4th edition, © 2010 McGraw-Hill, USA.

(pull-down NMOS transistors fights with load device)

A lower *equivalent* load resistance gives higher V_{OL} and hence degrading the noise margin NM_{L} (also <u>static</u> power consumption) though it produces faster rising output.

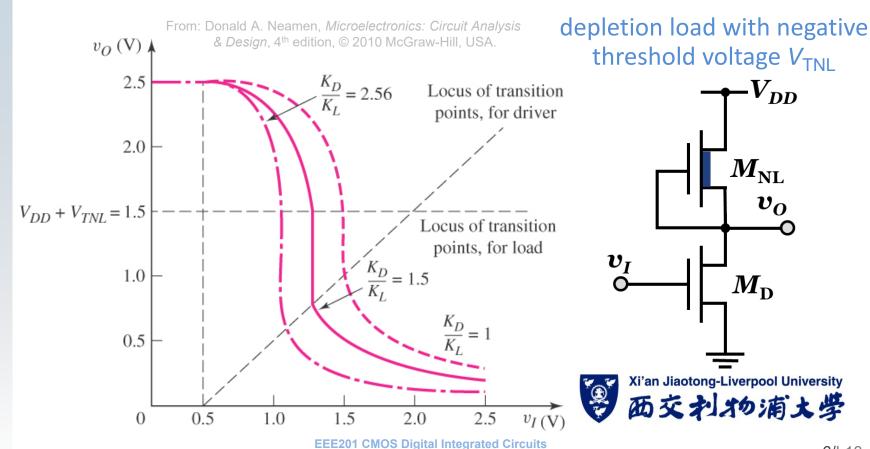


西交利物浦大学

VTC of NMOS Inverters

(depletion load with negative V_{TN})

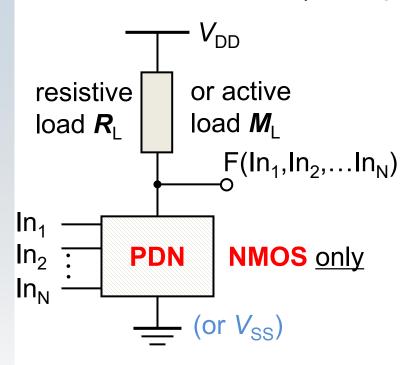
□ In the case of using a depletion-mode nMOSFET as the load device, VTC are better for certain gain factor (K_D, K_L) ratios.



Semester 1, 2024/2025 by S.Lam@XJTLU

(ratioed load resistance or transistor size)

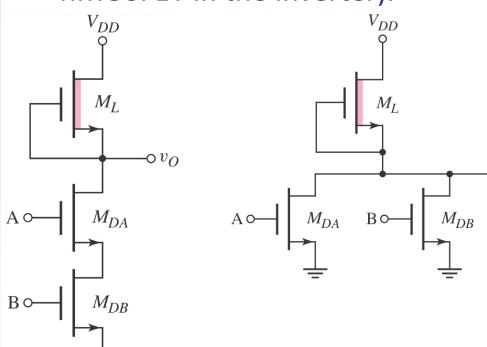
□ With the <u>static</u> load, the proper operation of the NMOS logic circuits depends on the appropriate load resistance R_{\perp} or transistor size (i.e. W/L).

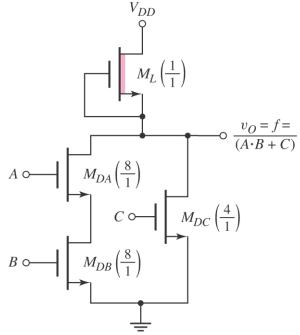


- Typically, the <u>static</u> load is a MOSFET. Its size and that of those NMOS transistors in the pull-down network (PDN) have a <u>ratio</u> constraint.
- □ Such logic circuits are called ratioed logic, with the logic function performed solely by the PDN. Xi'an Jiaotong-Liverpool University 西交利物消大學

(examples other than inverter)

■ Examples of ratioed logic have more than one NMOS transistors in the pull-down network (instead of one nMOSFET in the inverter).







From: Donald A. Neamen, *Microelectronics: Circuit Analysis & Design*, 4th edition, © 2010 McGraw-Hill, USA.

(disadvantages compared with CMOS)

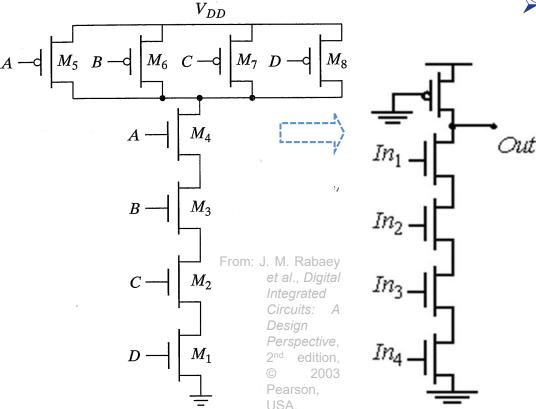
- □ Ratioed logic is generally not as good as CMOS logic circuits:
 - \triangleright It is less *robust* (in terms of fabrication variation from the components' nominal values and circuit operation), with a simple load device replacing the PUN which provides a conditional path between $V_{\rm DD}$ and the output when the PDN is turned off.
 - ➤ Static power dissipation in ratioed logic may not be acceptable when the number of logic gates increases; (think about 10 mA static current in each logic gate and there are 10k logic gates).
 - $> V_{\rm OL} > 0$ (hence $NM_{\rm L} = V_{\rm IL} V_{\rm OL}$ decreases) in ratioed logic circuit while CMOS has $V_{\rm OL} = 0$.

(less transistors & input capacitance)

- □ Despite the disadvantages compared with CMOS logic, ratioed logic is used in some special applications.
- □ Ratioed logic can be used to achieve certain purposes:
 - ➤ It reduces the number of transistors required to implement a given logic function.
 - If there are N inputs in a logic circuit, ratioed logic requires only N+1 MOSFETs but CMOS requires 2N.
 - > It reduces the input capacitances of the logic gates as pMOSFETs typically have much larger transistor size than nMOSFETs in CMOS logic and hence contributing much to the input capacitance. As a result, ratioed logic circuits can have a faster switching speed.

(4-input NAND gate example)

☐ The reduced number of MOSFETs can be seen in an example of a four-input NAND gate.



➤ 4 inputs require only5 MOSFETs in ratioed logic but 8 in CMOS.

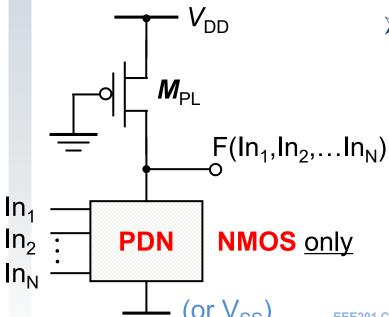
➤ Imagine the layout of the 4-input NAND gate and the chip area saved in replacing the 4-transistor PUN with one pMOSFET.



Ratioed Logic: pseudo-NMOS

(implemented in CMOS technology)

- Ratioed logic can be implemented in CMOS technology with a pMOSFET as the load device replacing the PUN.
 - \succ The gate of pMOSFET as the load device is grounded (or connected to the negative power supply V_{SS}).
- ☐ Such ratioed logic is referred to as pseudo-NMOS logic.



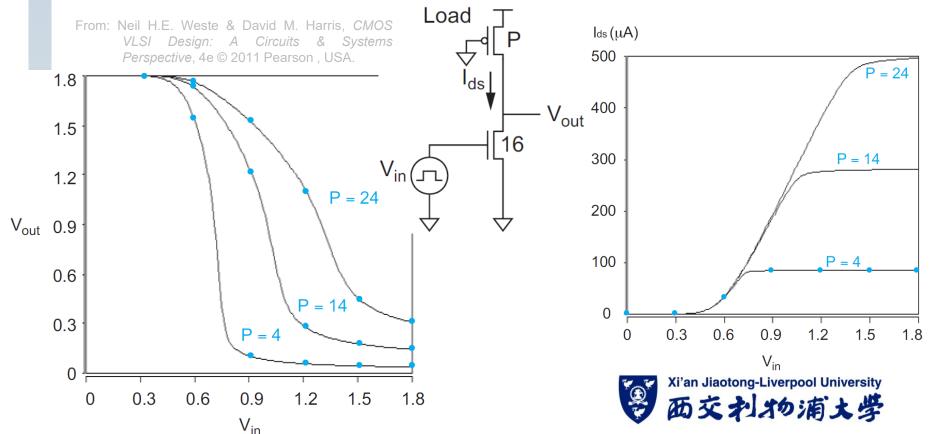
As expected in ratioed logic, the size of the pMOSFET relative to that of the nMOSFETs in the PDN can be used to <u>trade off</u> parameters such as noise margin, propagation delay, and power dissipation.

Xi'an Jiaotong-Liverpool University 面交利的消失學

Ratioed Logic: pseudo-NMOS

(pseudo NMOS inverter)

☐ The performance trade-off in the **pseudo-NMOS** logic can be seen in the simple case of a pseudo-NMOS inverter.



Ratioed Logic: pseudo-NMOS

(pseudo NMOS inverter)

1.0

0.5

√0.0 0.0 $W/L_{p} = 0.5$

 $W/L_p = 0.25$

0.5

☐ In a pseudo-NMOS inverter, the size of nMOSFET is

 $W/L_p = 2$

 W/L_p

1.0

 $0.5 \mu m / 0.25 \mu m$. $(W/L)_p$ **Static Power** t_{pLH} **Dissipation** (µW) 3.0 From: J. M. Rabaey et al., Digital Integrated Circuits: A Design 4 0.693 564 14 Perspective, 2nd edition, © 2003 Pearson, USA. 0.273 298 56 2 2.5 0.133 1 160 123 2.0 0.5 0.064 80 268 0.25 0.031 41 569 1.5

trade-off between power dissipation & propagation delay (hence speed)

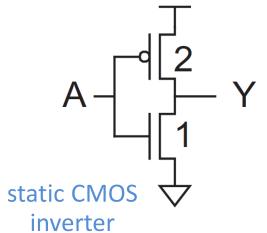


1.5 2.0 2.5 $V_{in}\left[V\right]$ EEE201 CMOS Digital Integrated Circuits Semester 1, 2024/2025 by S.Lam@XJTLU

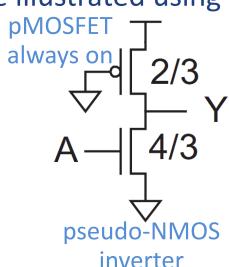
Pseudo-NMOS to Dynamic Logic

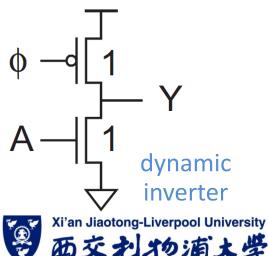
(overcoming static power dissipation)

- □ The drawbacks (especially the <u>static</u> power dissipation) of pseudo-NMOS can be overcome by using a <u>clocked</u> pull-up transistor rather than a pMOSFET that is always on.
 - ➤ Logic circuits with a <u>clocked</u> pull-up device are referred to as **dynamic logic**.
 - > The idea can be illustrated using the inverter case.



From: Neil H.E. Weste & David M. Harris, CMOS VLSI Design: A Circuits & Systems Perspective, 4e © 2011 Pearson, USA.



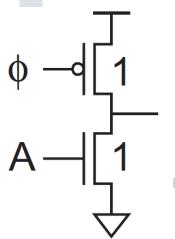


Dynamic Logic – precharge mode

(precharge & evaluation modes)

- ☐ The operation of the *dynamic* inverter is divided into two modes (or phases): **precharge** and **evaluation**, in sequence.
 - \triangleright The operation mode is determined by the clock input ϕ .





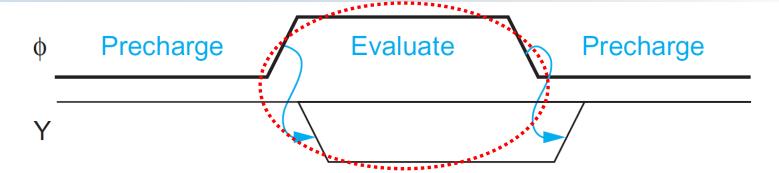
> During the **precharge** mode (i.e. when the clock ϕ is "0"), the clocked pMOSFET turns on and the output Y is **precharged** to V_{DD} .

From: Neil H.E. Weste & David M. Harris, CMOS VLSI Design: A Circuits & Systems Perspective, 4e © 2011 Pearson, USA.

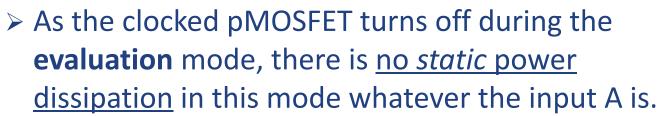


Dynamic Logic – evaluation mode

(no static power dissipation in evaluation mode)



 \triangleright During the **evaluation** mode (i.e. when the clock ϕ is "1"), the clocked pMOSFET turns off and the output Y may remain at V_{DD} or may be discharged to "0" through the pull-down network (an nMOSFET in the inverter case).



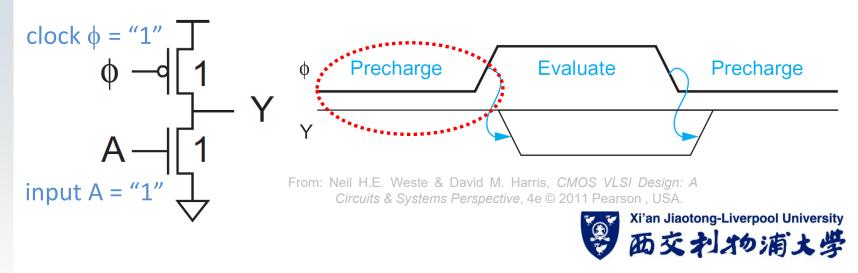
From: Neil H.E. Weste & David M. Harris, CMOS VLSI Design: A Circuits & Systems Perspective, 4e © 2011 Pearson, USA.



Dynamic Logic – precharge mode

(contention in pulling up & down)

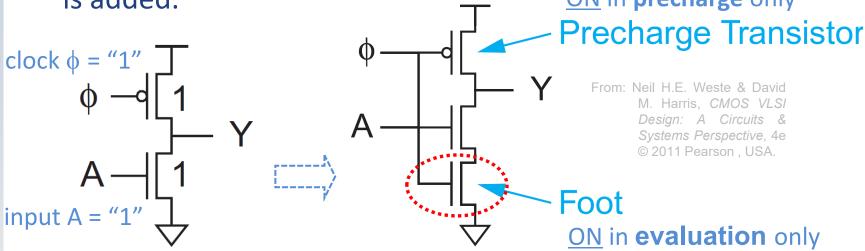
- ☐ With only the pull-up pMOSFET clocked, there can be problems during the **precharge** mode:
 - ➢ if the input A is "1" hence the pull-down nMOSFET turns on, both the pMOSFET and nMOSFET are on and contention will take place between them (i.e. the two MOSFETs fight to pull up or down the output voltage).



Dynamic Logic – precharge mode

(extra clocked evaluation transistor)

□ To avoid such a contention situation that both pull-up and pull-down MOSFETs turn on, an extra *evaluation* transistor is added. □ ON in precharge only



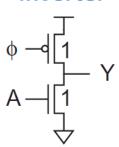
The extra clocked transistor is an nMOSFET stacked under the pull-down network (one nMOSFET in the inverter case). It is sometimes called a foot.
Xi'an Jiaotong-Liverpool University 西交利が消入学

(footed & unfooted logic gates)

■ Examples of dynamic logic gates with the extra clocked MOSFET is shown below:

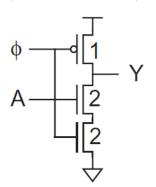
inverter

<u>unfooted</u> logic gates

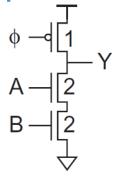


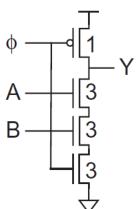
From: Neil H.E. Weste & David M. Harris, CMOS VLSI Design: A Circuits & Systems Perspective, 4e © 2011 Pearson, USA.

<u>footed</u> logic gates

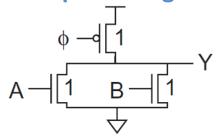


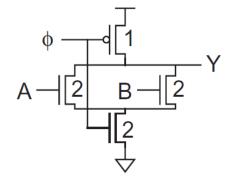
2-input NAND gate





2-input NOR gate

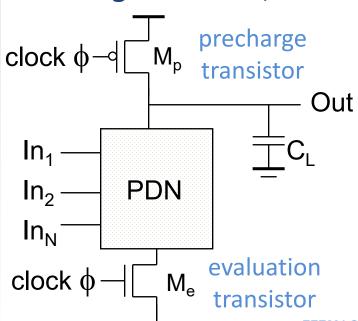






(footed & unfooted logic gates)

- ☐ In general, a **dynamic logic** circuit consists of three parts stacked on one another:
 - a clocked pMOSFET (called a precharge transistor);
 - ➤ a pull-down network (PDN) of nMOSFETs for performing logic function; it is exactly the same as that in CMOS logic;



- ➤ a clocked nMOSFET (called a foot or evaluation transistor).
- ➤ The number of MOSFETs required for implementing a logic circuit of *N* inputs is *N*+2 which is generally smaller than 2*N* in CMOS logic.



(important properties)

- □ Several important properties can be derived for the dynamic logic:
 - ➤ It is <u>non-ratioed</u>: the size of the precharge pMOSFET is not important for the correct operation of the logic gates; the size of the pMOSFET can be made large to improve the low-to-high transition time (but at a cost to the high-to-low transition time).
 - > It consumes only *dynamic* power. Ideally, there is no static current path exists between $V_{\rm DD}$ and the ground.

 - $ightharpoonup V_{OL}$ is ground (or V_{SS}) & $V_{OH} = V_{DD}$.

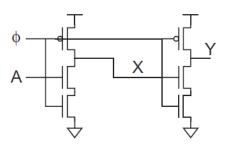
 EEE201 CMOS Digital Integrated Circuits

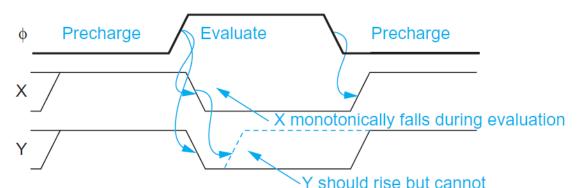
 Semester 1, 2024/2025 by S.Lam@XJTLU

(monotonicity problem)

- □ Despite the apparent advantages (especially the faster switching speed and zero static power dissipation) of the dynamic logic, it suffers from monotonicity problem:
 - > During evaluation, the inputs must be monotonically rising; they cannot start "1" and fall to "0".

Neil H.E. Weste & David M. Harris, *CMOS VLSI Design: A Circuits & Systems Perspective*, 4e © 2011 Pearson, USA.





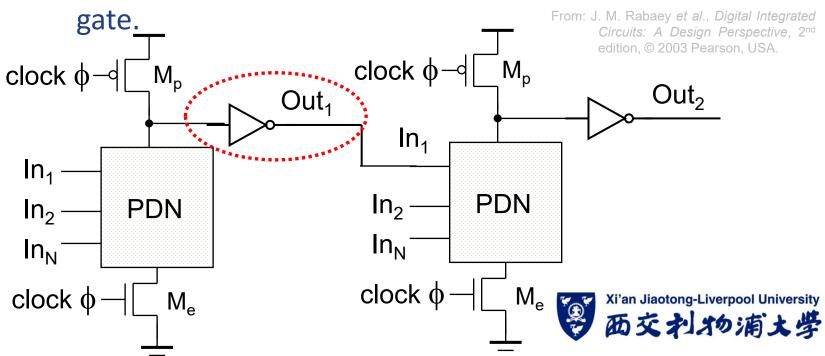
The problem can be seen in cascaded dynamic logic gates.



Domino CMOS Logic

(monotonicity problem)

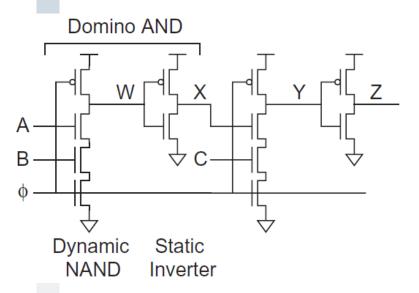
- ☐ The monotonicity problem in the **dynamic logic** can be resolved by placing a static CMOS inverter between the dynamic logic gates.
 - > The dynamic-static pair together is called a domino logic

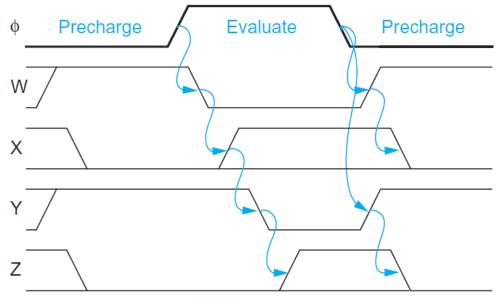


Domino CMOS Logic

(like dominos tipping over)

The name domino logic derives from the fact that precharge resembles setting up a chain of dominos and evaluation causes the logic gates to fire like dominos tipping over, each triggering the next. From: Neil H.E. Weste & David M. Harris, CMOS VLSI Design: A Circuits & Systems Perspective, 4e © 2011 Pearson, USA.





➤ This can be illustrated using a two cascading domino AND gates.



Pseudo-NMOS to Dynamic Logic

(comparisons with CMOS logic)

- ☐ The **domino logic** is developed from **dynamic logic** which is in turn from pseudo-NMOS (which is ratioed logic and has static power dissipation problems).
 - > Their comparisons can be seen using a 2-input NAND gate.

